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**IN THE TITLE:**

Please delete the title SYSTEM AND METHOD FOR OXONE CLEANING A LIQUID CRYSTAL DISPLAY STRUCTURE and substitute therefor the title SYSTEM AND METHOD FOR FORMING OZONE RESISTANT IC AND LCD STRUCTURES.

**IN THE CLAIMS:**

✓ Please cancel claim 2, 3, 19, 20, and 25.

Please amend claims 1, 8, 18, 22, and 24 as follows.

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1. (Currently Amended) In the fabrication of integrated circuit (IC) structures, a method for forming a structure resistant to ozone stripping, the method comprising:  
forming a first electrically conducting layer from indium tin oxide (ITO);  
forming an ozone resistant barrier overlying the first electrically conducting layer from a material selected from the group including Ta, Ti, TaN, Al, Al compounds, tungsten, and copper; and,  
forming a metal layer overlying the ozone resistive barrier.

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4. (Original) The method of claim 1 wherein forming a metal layer overlying the ozone resistant barrier includes forming a reflective metal layer from Al.

5. (Original) The method of claim 4 wherein forming a metal layer overlying the ozone resistant barrier includes forming a layer of Al having a thickness of greater than 1000 Å.

6. (Original) The method of claim 1 in which a reflective liquid crystal display (LCD) IC structure is formed;  
wherein forming a first electrically conducting layer includes forming an electrode; and,  
wherein forming a metal layer overlying the ozone resistant barrier includes forming an LCD reflector.

7. (Original) The method of claim 1 in which a busline IC structure is formed; and,  
wherein forming a metal layer overlying the ozone resistant barrier includes forming the top metal layer of a busline.

8. (Currently Amended) In the fabrication of liquid crystal displays (LCDs) integrated circuits (ICs), a method for forming a LCD structure resistant to ozone stripping, the method comprising:  
forming an indium tin oxide (ITO) layer electrode;  
forming an ozone resistant barrier overlying the electrode from a material selected from the group including Ti, Ta, ~~TiN~~, and TaN;  
and,  
forming an Al reflector overlying the ozone resistant barrier.

18. (Currently Amended) A liquid crystal display (LCD) reflector structure resistant to ozone stripping, the reflector structure comprising:  
a first electrically conducting layer of indium tin oxide (ITO);

an ozone resistive barrier overlying the first electrically conducting layer from a material selected from the group including Ti, Ta, TaN, Al, Al compounds, tungsten, and copper; and,  
a metal layer overlying the ozone resistive barrier.

21. (Original) The reflector structure of claim 18 wherein the metal layer is a reflective metal layer material selected from the group including Al.

22. (Currently Amended) A liquid crystal display (LCD) reflector structure resistant to ozone stripping, the reflector structure comprising:  
a first electrically conducting layer of indium tin oxide (ITO);  
an ozone resistive barrier overlying the first electrically conducting layer selected from the group including Ti, Ta, ~~TiN~~, TaN, Al, Al compounds, tungsten, ~~chrome~~, and copper; and,  
an Al reflective metal layer overlying the ozone resistive barrier.

23. (Original) A liquid crystal display (LCD) reflector structure resistant to ozone stripping, the reflector structure comprising:  
a first electrically conducting layer selected from the group including Ti, Ta, and Al; and,  
a reflective metal layer overlying the first electrically conducting layer selected from the group including Al.

24. (Currently Amended) In the fabrication of integrated circuit (IC) structures, a method for forming a structure resistant to ozone stripping, the method comprising:

forming a first electrically conducting layer from a material selected from the group including Ti, Ta, and Al; and,

forming a metal layer overlying the electrically conducting layer.

26. (Original) The method of claim 24 wherein forming a metal layer overlying the first electrically conducting layer includes forming a reflective metal layer from Al.

27. (Original) The method of claim 26 wherein forming a metal layer overlying the first electrically conducting layer includes forming a layer of Al having a thickness of greater than 1000 Å.

28. (Original) The method of claim 24 in which a reflective liquid crystal display (LCD) IC structure is formed;

wherein forming a first electrically conducting layer includes forming an electrode; and,

wherein forming a metal layer overlying the first electrically conducting layer includes forming an LCD reflector.

29. (Original) The method of claim 24 in which a busline IC structure is formed; and,

wherein forming a metal layer overlying the first electrically conducting layer includes forming the top metal layer of a busline.